

# BUK753R8-80E

## N-channel TrenchMOS standard level FET

11 September 2012

Product data sheet

## 1. Product profile

### 1.1 General description

Standard level N-channel MOSFET in a SOT78 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

### 1.2 Features and benefits

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with VGS(th) rating of greater than 1V at 175 °C

### 1.3 Applications

- 12V, 24V and 48V Automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	80	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <a href="#">Fig. 1</a>	[1]	-	-	120	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <a href="#">Fig. 2</a>		-	-	349	W
<b>Static characteristics</b>							
R <sub>DS(on)</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 11</a>		-	3.3	4	mΩ
<b>Dynamic characteristics</b>							
Q <sub>GD</sub>	gate-drain charge	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 64 V; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a>		-	51	-	nC

[1] Continuous current is limited by package.

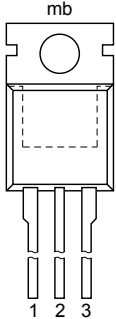
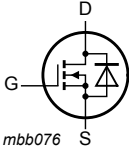


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## 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 TO-220AB (SOT78A)	 mbb076
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

## 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK753R8-80E	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78A

## 4. Marking

Table 4. Marking codes

Type number	Marking code
BUK753R8-80E	BUK753R8-80E

## 5. Limiting values

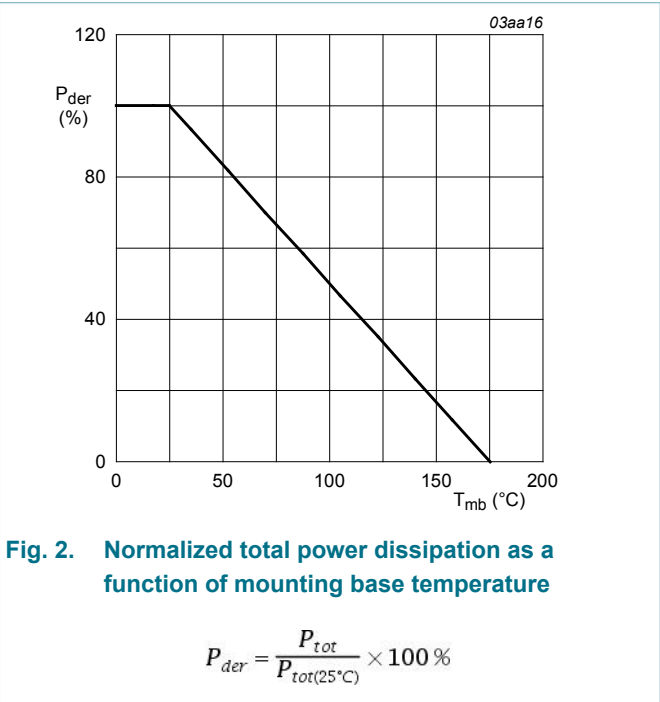
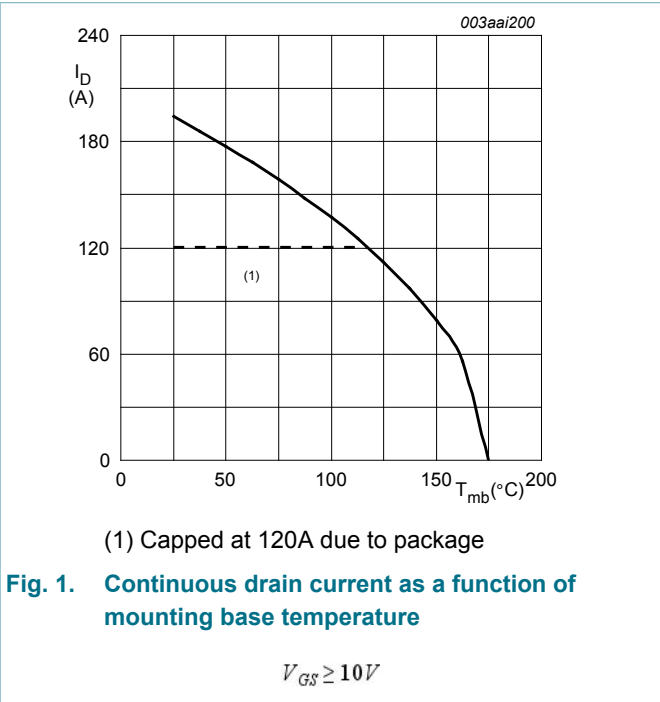
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ }^\circ\text{C}$ ; $T_j \leq 175\text{ }^\circ\text{C}$		-	80	V
$V_{DGR}$	drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$		-	80	V
$V_{GS}$	gate-source voltage	$T_j = 175\text{ }^\circ\text{C}$ ; DC		-20	20	V
$I_D$	drain current	$T_{mb} = 25\text{ }^\circ\text{C}$ ; $V_{GS} = 10\text{ V}$ ; Fig. 1	[1]	-	120	A
		$T_{mb} = 100\text{ }^\circ\text{C}$ ; $V_{GS} = 10\text{ V}$ ; Fig. 1	[1]	-	120	A
$I_{DM}$	peak drain current	$T_{mb} = 25\text{ }^\circ\text{C}$ ; pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; Fig. 4		-	758	A

Symbol	Parameter	Conditions		Min	Max	Unit
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <a href="#">Fig. 2</a>		-	349	W
T <sub>stg</sub>	storage temperature			-55	175	°C
T <sub>j</sub>	junction temperature			-55	175	°C
Source-drain diode						
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	<a href="#">[1]</a>	-	120	A
I <sub>SM</sub>	peak source current	pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C		-	758	A
Avalanche ruggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	I <sub>D</sub> = 120 A; V <sub>sup</sub> ≤ 80 V; R <sub>GS</sub> = 50 Ω; V <sub>GS</sub> = 10 V; T <sub>j(init)</sub> = 25 °C; unclamped; <a href="#">Fig. 3</a>	<a href="#">[2][3]</a>	-	488	mJ

- [1] Continuous current is limited by package.
- [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [3] Refer to application note AN10273 for further information.



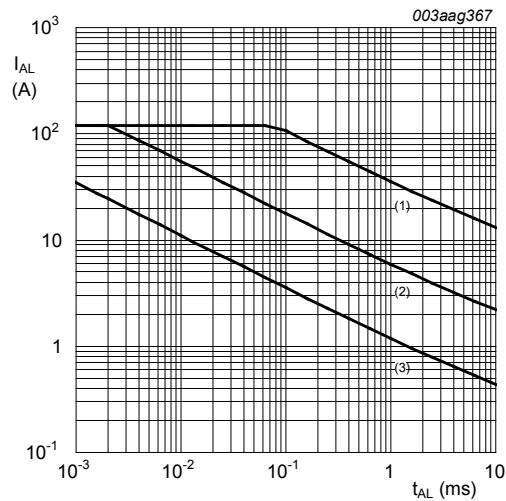


Fig. 3. Avalanche rating; avalanche current as a function of avalanche time.

(1)  $T_{j(jnt)} = 25^{\circ}\text{C}$ ; (2)  $T_{j(jnt)} = 150^{\circ}\text{C}$ ; (3) Repetitive Avalanche

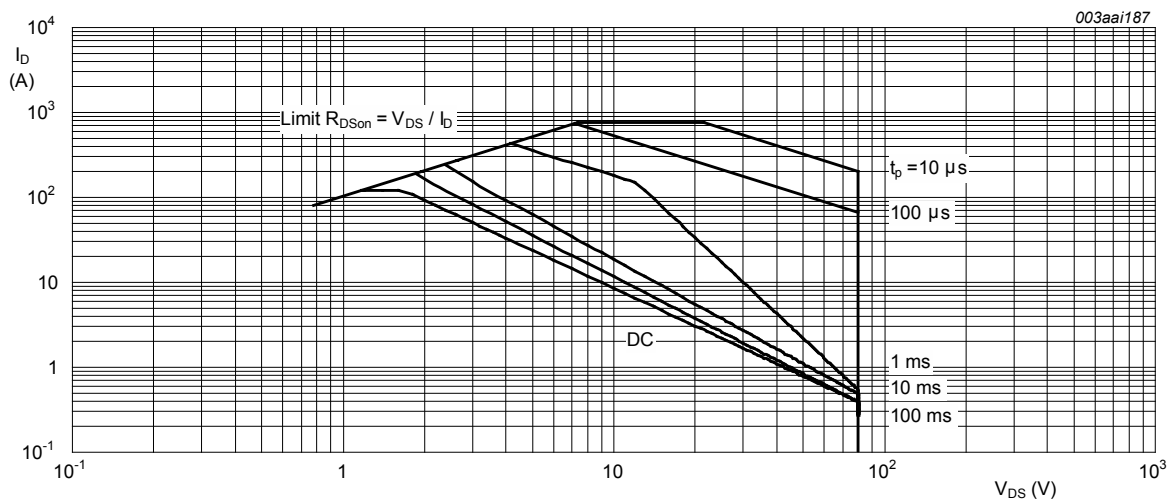


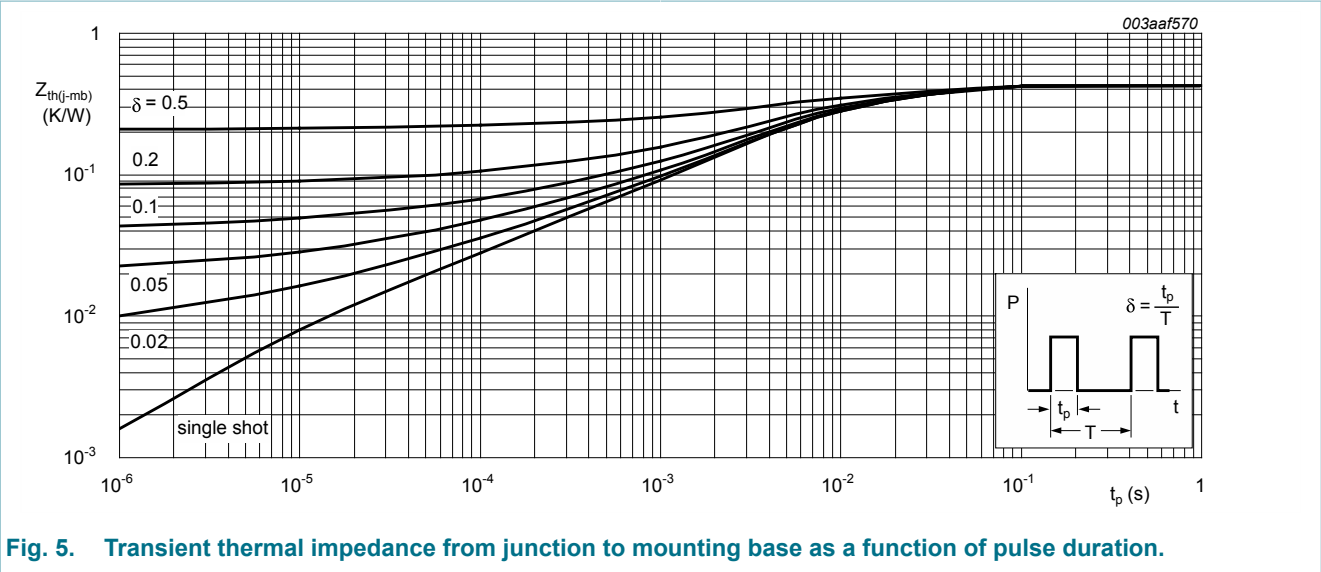
Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25^{\circ}\text{C}$ ;  $I_{DM}$  is a single pulse

## 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5	-	-	0.43	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in still air	-	60	-	K/W

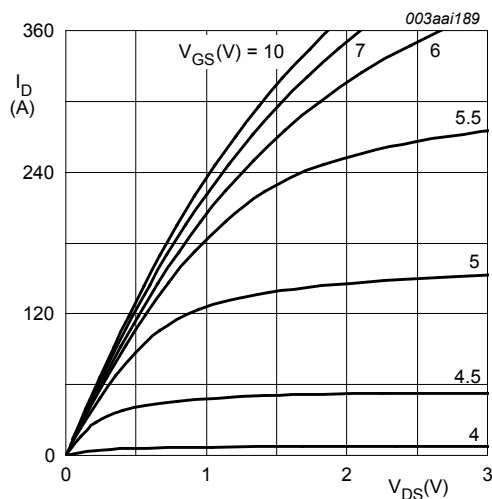


7. Characteristics

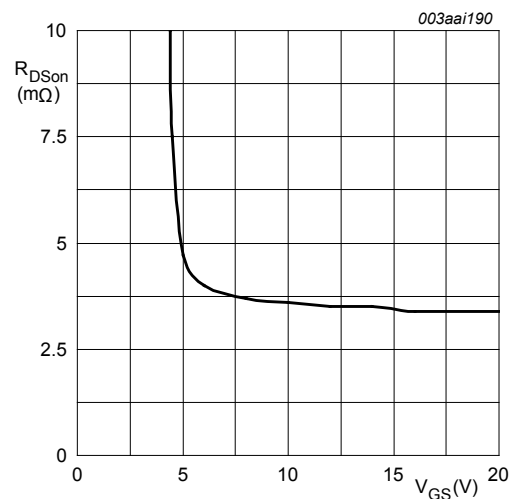
Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>J</sub> = 25 °C		80	-	-	V
		I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>J</sub> = -55 °C		72	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>J</sub> = 25 °C; <a href="#">Fig. 9</a> ; <a href="#">Fig. 10</a>		2.4	3	4	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>J</sub> = 175 °C; <a href="#">Fig. 9</a>		1	-	-	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>J</sub> = -55 °C; <a href="#">Fig. 9</a>		-	-	4.5	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 80 V; V <sub>GS</sub> = 0 V; T <sub>J</sub> = 25 °C		-	0.15	2	μA
		V <sub>DS</sub> = 80 V; V <sub>GS</sub> = 0 V; T <sub>J</sub> = 175 °C		-	-	500	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>J</sub> = 25 °C		-	2	100	nA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>J</sub> = 25 °C		-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>J</sub> = 25 °C; <a href="#">Fig. 11</a>		-	3.3	4	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>J</sub> = 175 °C; <a href="#">Fig. 12</a> ; <a href="#">Fig. 11</a>		-	-	9.7	mΩ
Dynamic characteristics							
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 64 V; V <sub>GS</sub> = 10 V; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a>		-	169	-	nC
Q <sub>GS</sub>	gate-source charge			-	37	-	nC
Q <sub>GD</sub>	gate-drain charge			-	51	-	nC

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$C_{iss}$	input capacitance	$V_{GS} = 0\text{ V}$ ; $V_{DS} = 25\text{ V}$ ; $f = 1\text{ MHz}$ ;		-	9020	12030	pF
$C_{oss}$	output capacitance	$T_j = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 15</a>		-	840	1010	pF
$C_{rss}$	reverse transfer capacitance			-	470	645	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 60\text{ V}$ ; $R_L = 2.4\text{ }\Omega$ ; $V_{GS} = 10\text{ V}$ ; $R_{G(ext)} = 5\text{ }\Omega$		-	38	-	ns
$t_r$	rise time			-	48	-	ns
$t_{d(off)}$	turn-off delay time			-	129	-	ns
$t_f$	fall time			-	65	-	ns
$L_D$	internal drain inductance	from drain lead 6mm from package to centre of die		-	4.5	-	nH
		from upper edge of mounting base to centre of die		-	2.5	-	nH
$L_S$	internal source inductance	from source lead to source bond pad		-	7.5	-	nH
<b>Source-drain diode</b>							
$V_{SD}$	source-drain voltage	$I_S = 25\text{ A}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 16</a>		-	0.77	1.2	V
$t_{rr}$	reverse recovery time	$I_S = 20\text{ A}$ ; $dI_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ;		-	58	-	ns
$Q_r$	recovered charge	$V_{DS} = 25\text{ V}$		-	121	-	nC



**Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values**



**Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values**

$T_j = 25\text{ }^{\circ}\text{C}$ ;  $I_D = 25\text{ A}$

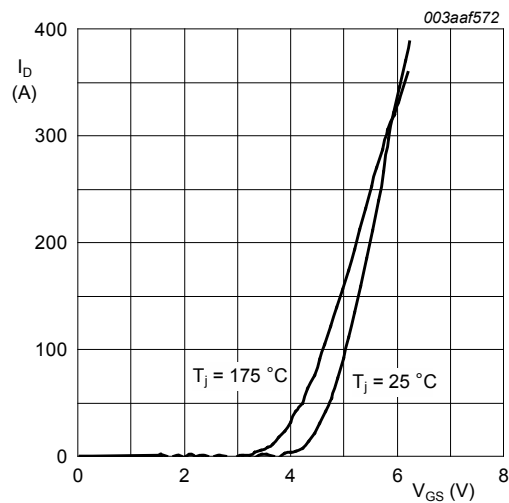


Fig. 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$V_{DS} = 12\text{ V}$

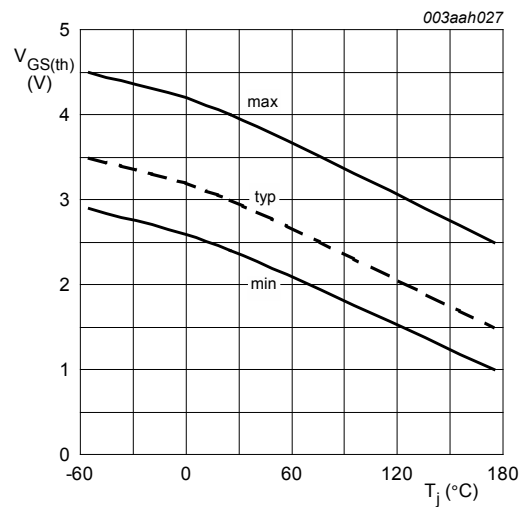


Fig. 9. Gate-source threshold voltage as a function of junction temperature

$I_D = 1\text{ mA}; V_{DS} = V_{GS}$

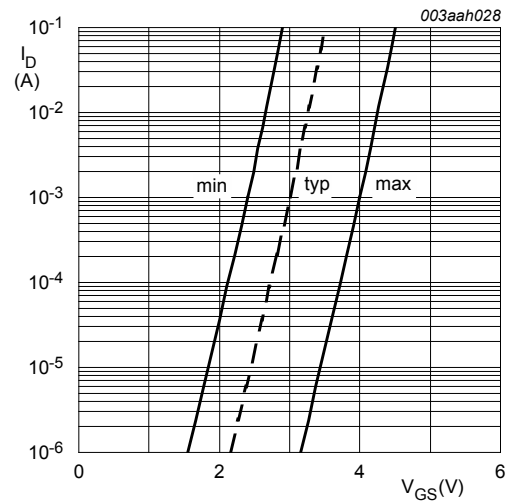


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$T_J = 25\text{ }^{\circ}\text{C}; V_{DS} = 5\text{ V}$

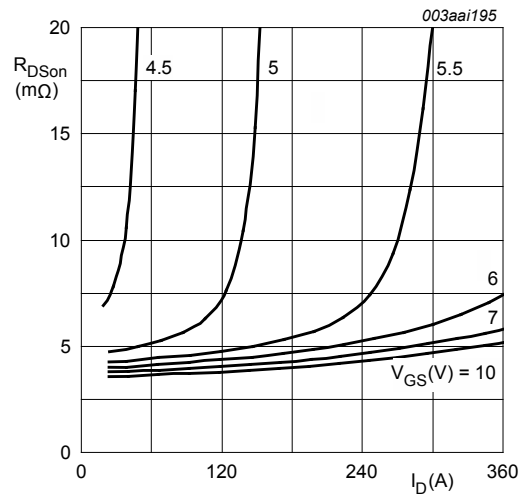


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

$T_J = 25\text{ }^{\circ}\text{C}; t_p = 300\text{ }\mu\text{s}$

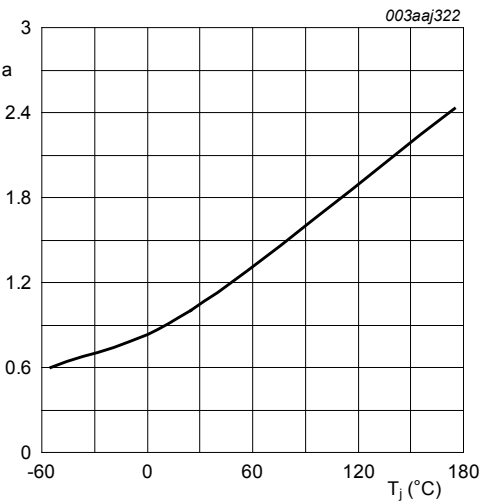
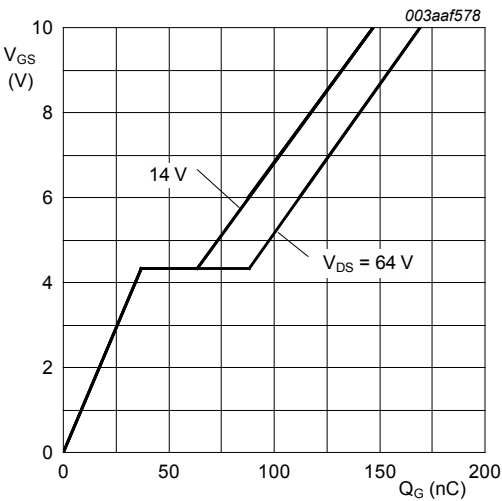


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DS(on)}}{R_{DS(on)}(25^{\circ}\text{C})}$$



$T_j = 25^{\circ}\text{C}; I_D = 25\text{ A}$

Fig. 13. Gate-source voltage as a function of gate charge; typical values

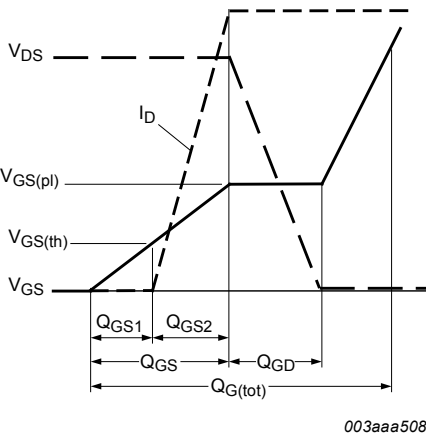
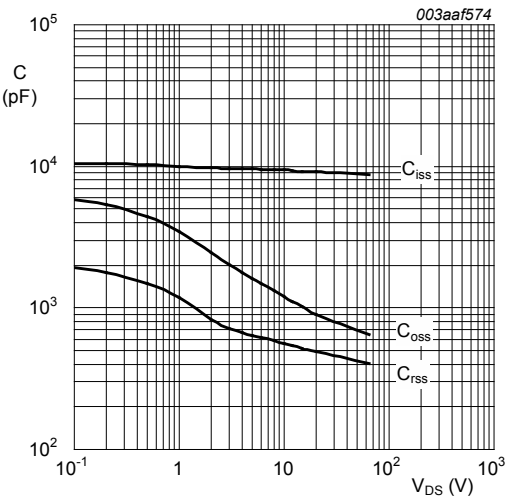


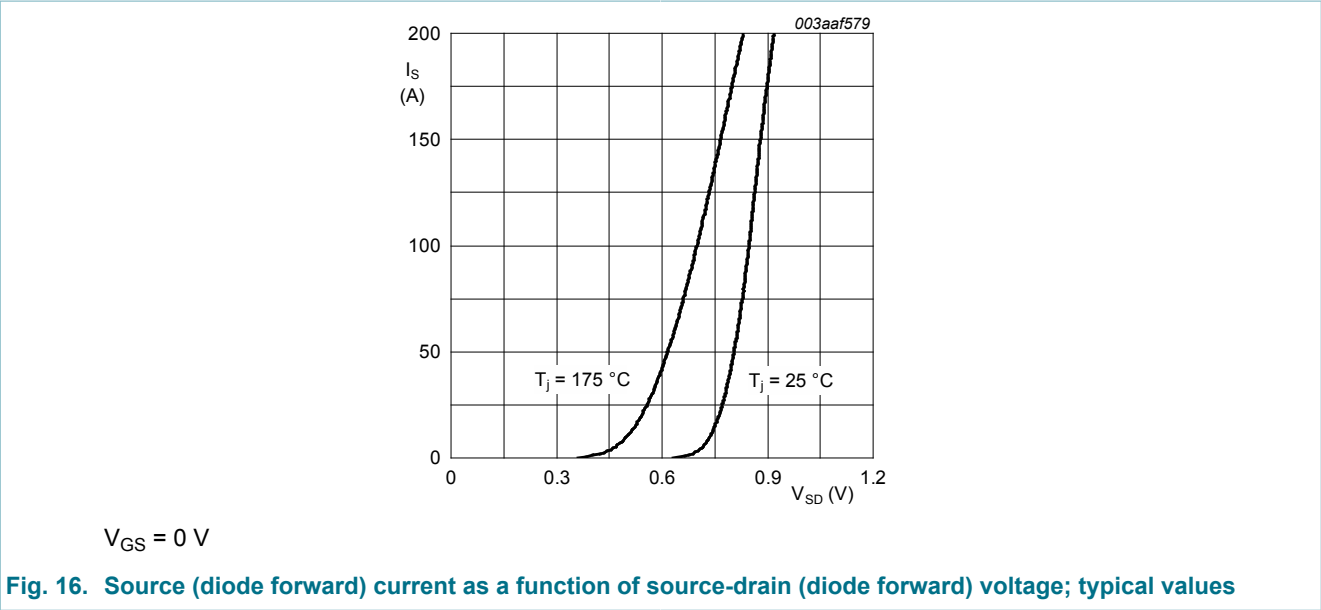
Fig. 14. Gate charge waveform definitions



$V_{GS} = 0\text{ V}; f = 1\text{ MHz}$

Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values





8. Package outline

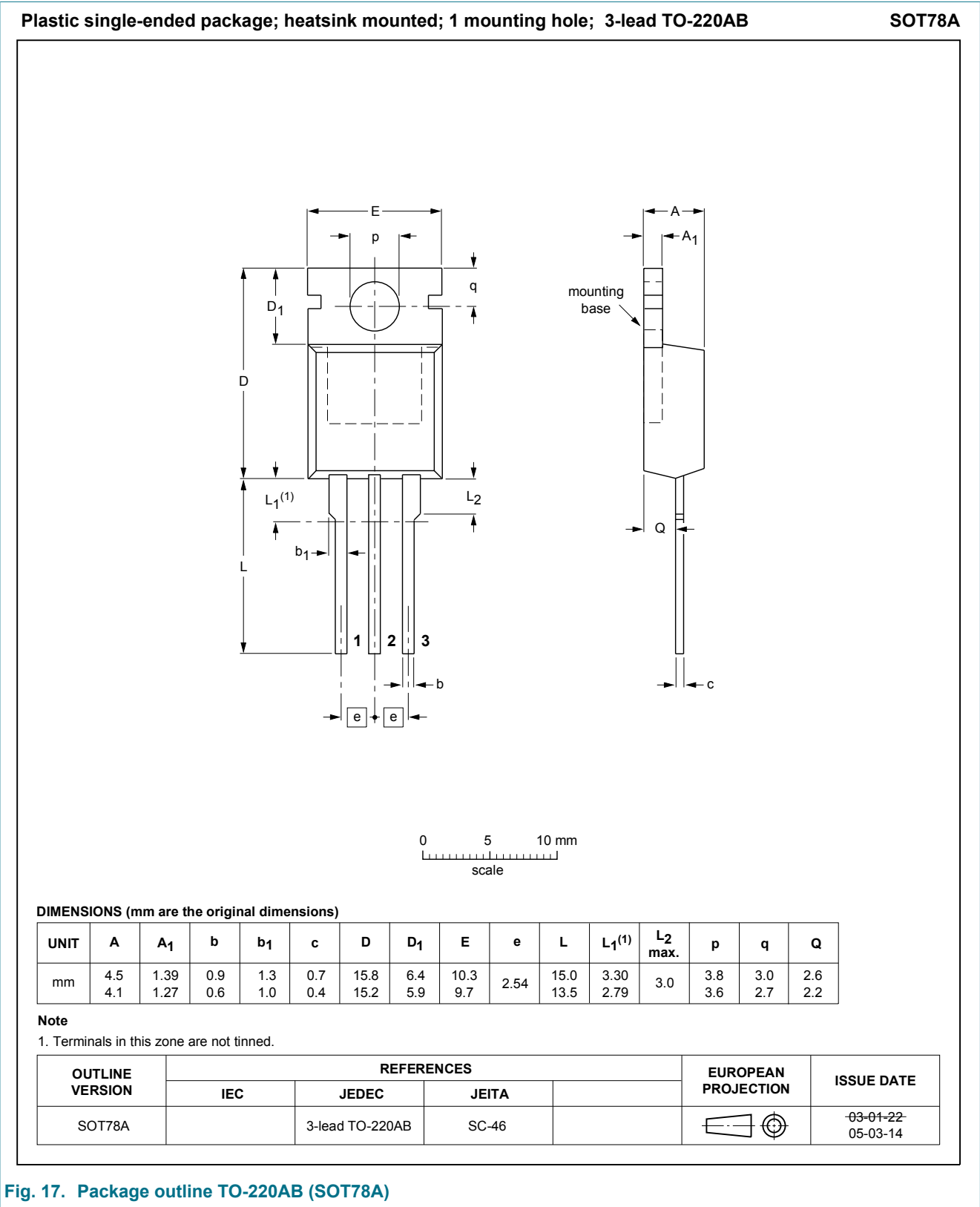


Fig. 17. Package outline TO-220AB (SOT78A)

## 9. Legal information

### 9.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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